**HEWLETT-PACKARD COMPANY** Intellectual Property Administration P. O. Box 272400 Fort Collins, Colorado 80527-2400

Ashton, et al.

Sept. 3, 2003

This Information Disclosure Statement is submitted:

under 37 CFR 1.97(b), or

Inventor(s):

Filing Date:

PO Box 1450

Title:

Sir:

Application No.:

**Commissioner for Patents** 

Alexandria, VA 22313-1450

ATTORNEY DOCKET NO. 100201669-1

Confirmation No.:

**Group Art Unit:** 

**Examiner:** 

### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT

(Within three months of filing national application; or date of entry of national application; or before

CELLS AND METHODS OF FABRICATION THEREOF

mailing date of first office action on the merits; whichever occurs last)

ULTRA-HIGH DENSITY STORAGE DEVICE USING PHASE CHANGE DIODE MEMORY

( ) under 37 CFR 1.97 (d) together with ( ) Statement under 37 CFR 1.97(e) ( ) a \$180.00 fee set forth in 37 CF	n, or 7(p), or re final action or notice of allowance, whichever occurs first) a: o(1) or (2), and
Please charge to Deposit Account <b>08-2025</b> pendency of this application, please charge an Account <b>08-2025</b> pursuant to 37 CFR 1.25.	5 the sum of \$0.00 . At any time during the y fees required or credit any overpayment to Deposit
copies, of patents, publications or other informa	O 1449 - Information Disclosure Citation together with tion of which applicant(s) are aware, which applicant(s) f this application and for which there may be a duty to
and other foreign language information listed individuals(s) designated in 37 CFR 1.56 (c) mattached sheet, or where a foreign language process patent office in a counterpart foreign seems.	foreign language patents, foreign language publications on PTO Form 1449, as presently understood by the lost knowledgeable about the content is given on the patent is cited in a search report or other action by a application, an English language version of the search levance found by the foreign office is listed on form PTO
It is requested that the information disclosed her	ein be made of record in this application.
"Express Mail" label no. EL 980208664 US	Respectfully submitted,
Date of Deposit Sept. 3, 2003	Ashton, et al.
I hereby certify that this is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated above and is addressed to: Commissioner for Patents, Washington, D.C.	Vaughn W. North

Date: Sept. 3, 2003 Telephone No.: (801) 566-6633

Attorney/Agent for Applicant(s) 27,930

Reg. No.

Rev 05/03 (IDSXML)

Typed Name: Vaughn W. North

20231.

Sheet 1 of 5

	DM D	TO 1449			ATTY. DOCKET NO.	APPLICATION NO	CONFIRMAT	TION NO	
FORM PTO-1449  LIST OF PATENTS AND PUBLICATIONS FOR					100201669-1				
			UBLICATIONS FOR ION DISCLOSURE		APPLICANT				
		STATI	EMENT		Ashton, et al	GROUP			
	(Us	se several sheets	if necessary)		Sept. 3, 2003				
REFERE	NCE [	DESIGNATION	U.S. P	ATEN	T DOCUMENTS				
EX A MINER INITIA L		DOCUMENT NUMBER	PUBLICATION DATE		NAME	Pages, Columr Relevant Passages	ns, Lines Where or Figures App	ear	
*	1A 5	5,557,596	09/17/96	Gib	oson et al				
	1B 6	5,256,224	07/03/01	Per	ner, et al.				
	1C 6	5,262,421	07/17/01	Tra	าก				
	1D								
	1E			1-					
	1F			_					
	1G		<del> </del>	+					
	1H								
	11							<del></del>	
	1J								
	<del></del> +							<del>_</del>	
	1K								
	1		<del></del>		PATENT DOCUM			Check i	
		DOCUMENT NUMBER	PUBLICATION DATE	N	OR APPLICANT	Pages/Columns/Lir Relevant Passages/Fig		Translatio attached	
	1L							<u> </u>	
	1M							<u> </u>	
	1N							<u> </u>	
	10								
	1P								
		OTHER REI	FERENCES (includ	ing Au	uthor, Title, Date, F	Pertinent Pages, etc.	)		
	1Q	Kampmann, G Using a ITO	et al. A Cadmium-fre n2Se3/CulnSe2/Au	ee Culi Struct	nSe2 Superstrate Sol ure; Progress in Phot	ar Cell Fabricated by Ecovoltaics; (1999) pgs.	Electrodepositi 129-135.	on	
	1R	Rechid, et al. Solid Films; (	Characterising Sup 2000) pgs. 361-362	erstrat 2.	e CIS solar cells with	n electron beam induce	ed current; Th	in	
	18	Ward, et al. (10/01.	Cu(In,Ga)Se2 Thin-F	ilm Co	oncentrator Solar Cell	s; NCPV Program Rev	iew Meeting;		
EXAM	IINER				DATE CONSIDE	RED		_ <del>_</del>	

Sheet 2 of 5

FORM PT	0-1449			TTY. DOCKET NO. 00201669-1	APPLICATIO	ON NO.	CONFIRMA	TION NO
LIST OF F	PATENTS AND PU	BLICATIONS FOR		APPLICANT				
APPLICA	NT'S INFORMATIO STATEN			Ashton, et al				
			FI	LING DATE	GROUP			
(Use	e several sheets if	necessary)	S	ept. 3, 2003				
REFERENCE DESIGNATION U.S. PATE				ENT DOCUMENTS				
XAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE		NAME	Pages, C Relevant Pas	Columns ssages o	s, Lines Where or Figures App	e pear
2A	ļ							
2B								<del></del>
2C								<del></del>
2D								
2E								
2F								
2G				_				
2H								
21								
2J								
2K								
	DOCUMENT NUMBER	PUBLICATION DATE	NAM	ATENT DOCUME E OF PATENTEE R APPLICANT	Pages/Colum Relevant Passag			Check in Translation attached
2L								
2M								
2N								
20								
2P								
- ' '	OTHER REFE	RENCES (includir	ng Auth	or, Title, Date, P	ertinent Pages,	, etc.)		
2Q	Scofield, et al. polycrystalline	Sputtered molybde thin-film solar cells	enum bila ; Thin So	ayer back contact blid Films (1995) p	for copper indiun gs. 26-31	n disele	enide-based	
2R	Gabor, et al. H films; America	igh-efficiency Culna n Institute of Physic	xGa1·xS cs, (1994	e2 solar cells mad 4) pgs. 198-200	e from (Inx,Ga1-	x)2Se3	3 precursor	
28	Nakayama, et semiconductor	al. AES, LEELS and s GaSe and InSe; S	I XPS stu Surface S	udies on the interfa science (1991)	ace formation be	tw een	layered	

Rev 05/03 (PT01449)

Sheet 3 of 5

FC	ORM PT	O-1449		ATTY. DOCKET NO 100201669-1	. APPLICATION NO. CONFIRMAT	ION NO			
		PATENTS AND PU NT'S INFORMATIO STATEN	N DISCLOSURE	APPLICANT  Ashton, et al	Ashton, et al FILING DATE GROUP				
	(Us	se several sheets if	necessary)	Sept. 3, 2003					
EFERE	NCE E	DESIGNATION	U.S. PA	TENT DOCUMENTS					
AMINER NITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appe	ear			
	ЗА								
	3B								
	3C								
	3D								
	3E								
	3F								
	3G								
	ЗН								
	31								
	31								
	зк								
	3L	NUMBER	DATE	OR APPLICANT	Relevant Passages/Figures Appear	attach			
	ЗМ								
	3N								
	30								
	ЗР								
		OTHER REFE	RENCES (includin	ng Author, Title, Date,	Pertinent Pages, etc.)				
	ЗQ	Nishida, et al. 3 American Insitu	Single-beam overwi ute of Physics (198	rite experiment using In- 7) pgs. 667-669	Se based phase-change optical media;				
	3R	Sanchez-Royo, et al. Optical and photovoltaic properties of indium selenide thin films prepared by van der Waals epitaxy; Journal of Applied Physics (2001) pgs. 2818-2823							
	38	Otsmane, et al 479-481	. Epitaxy of layered	I semiconductor thin film	ns; Applied Surface Science (1993) pgs	<del></del> S.			
EXAM	INER			DATE CONSID	DERED	<del></del>			

Sheet 4 of 5

1 14	RM PT	0-1449	-	ATTY. DOCKET NO. 100201669-1	APPLICATION NO. CONFIRMA	TION NO	
LI:	ST OF F	ATENTS AND PU	BLICATIONS FOR	APPLICANT			
AF	PPLICAI	NT'S INFORMATIO STATEM		Ashton, et al			
	(Us	e several sheets if	necessary)	FILING DATE Sept. 3, 2003	GROUP		
REFERE	NCE D	ESIGNATION	U.S. PA	TENT DOCUMENTS		<del></del>	
XAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NA ME	Pages, Columns, Lines Wher Relevant Passages or Figures Ap	e pear	
	4A						
****	4B						
	4C						
	4D						
	4E						
	4F						
	4G						
	4H						
	41						
	4J						
	4K						
		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENT OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translatio	
	+						
	14L I					1	
-	4L 4M					-	
	4M						
	4M 4N						
	4M 4N 40	OTHER REFE	RENCES (including	ng Author, Title, Date, F	Pertinent Pages, etc.)		
	4M 4N 40	Emeny et al R	eflection high-energ	gy electron diffraction stud	Pertinent Pages, etc.)  dies of InSe and GaSe layered pplied Physics (1992) pgs. 3256-3	259	
	4M 4N 4O 4P	Emery, et al. R compounds gro	eflection high-energown by molecular b	gy electron diffraction stuc eam epitaxy; Journal of A	lies of InSe and GaSe lavered		
	4M 4N 4O 4P 4Q	Emery, et al. R compounds gro	eflection high-energown by molecular b al. Heteroepitaxy b pgs. 539-543	gy electron diffraction stuc peam epitaxy; Journal of A petween layered semicondu	lies of InSe and GaSe layered pplied Physics (1992) pgs. 3256-3	race	

Sheet 5 of 5

		· · · · · · · · · · · · · · · · · · ·	1.6	TTY, DOCKET NO.	APPLICATION NO	CONFIRMATI	ON NO	
RM PTO	)-1449							
			7	APPLICANT				
LICAN			1	Ashton, et al	I CPAUP			
(Use	several sheets if	necessary)		Sept. 3, 2003				
CE D	ESIGNATION	U.S. PA	TENT	DOCUMENTS				
	DOCUMENT NUMBER	PUBLICATION DATE		NAME	Pages, Column Relevant Passages	ns, Lines Where or Figures Appe	ar	
5A								
5B								
5C								
5D								
5E								
5F								
5G								
5H								
51			+				<del></del> -	
5.J			1					
		FOF	REIGN	PATENT DOCUME	ENTS			
	DOCUMENT NUMBER	PUBLICATION DATE			Pages/Columns/Lir Relevant Passages/Fig	nes Where gures Appear	Check if Translatio attached	
5L								
5M								
5N								
50								
5P								
<b>!</b>	OTHER REFE	RENCES (includi	ng Aut	hor, Title, Date, P	Pertinent Pages, etc.	.)		
5Q	Shigetomi, et a Journal of App	II. Electrical and ph lied Physics; (2000	otovolt )); pgs.	aic properties of Cu 1520-1524	-doped p-GaSe/n-InSe	heterojunction	 n;	
5R								
58							<del>.</del>	
NER	<u> </u>			DATE CONSIDE	RED			
	(Use CE D 5A 5B	CE DESIGNATION    DOCUMENT NUMBER	TOF PATENTS AND PUBLICATIONS FOR PAICANT'S INFORMATION DISCLOSURE STATEMENT  (Use several sheets if necessary)  CE DESIGNATION U.S. PA  DOCUMENT PUBLICATION DATE  5A  5B  5C  5F  5G  5H  5I  5J  5K   DOCUMENT PUBLICATION DATE  FOR  PORT  FOR  STATEMENT  FOR  STATEMENT  FOR  FOR  STATEMENT  STATEMENT	TOF PATENTS AND PUBLICATIONS FOR PLICANT'S INFORMATION DISCLOSURE STATEMENT  (Use several sheets if necessary)  CE DESIGNATION  DOCUMENT PUBLICATION DATE  DOCUMENT NUMBER  DOCUMENT PUBLICATION  DOCUMENT PUBLICATION  DOCUMENT PUBLICATION  FOREIGN  FOREIGN  FOREIGN  SI  SI  SI  SI  SI  SI  SI  SI  SI  S	TOP PATENTS AND PUBLICATIONS FOR APPLICANT SINFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)  CE DESIGNATION  U.S. PATENT DOCUMENTS  DOCUMENT PUBLICATION DATE  NAME  DOCUMENT NUMBER  DOCUMENT PUBLICATION NAME  DOCUMENT PUBLICATION NAME  DOCUMENT PUBLICATION NAME  FOREIGN PATENT DOCUMENTS  FOREIGN PATENT DOCUMENTS  FOREIGN PATENT DOCUMENT  NUMBER PUBLICATION NAME OF PATENTEE OR APPLICANT  DOCUMENT NUMBER  DOCUMENT NUMBER OR APPLICANT  SL SM SN	TOP PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT  (Use several sheets if necessary)  TOP DOCUMENT PUBLICATION DATE  DOCUMENT NUMBER  DATE  DOCUMENT NUMBER  DATE  FOREIGN PATENT DOCUMENTS  TOP DOCUMENT NUMBER  DOCUMENT DATE  DOCUMENT DATE  DOCUMENT DATE  DOCUMENT DATE  St. Shipetomi, et al. Electrical and photovoltaic properties of Cu-doped p-GaSe/h-inscreption of Applied Physics; (2000); pgs. 1520-1524  SS. Shipetomi, et al. Electrical and photovoltaic properties of Cu-doped p-GaSe/h-inscreption of Cu-doped p-GaSe/h-	TOP TATENTS AND PUBLICATIONS FOR FOR FOR FOR TATEMENT  (Use several sheets if necessary)  CE DESIGNATION  U.S. PATENT DOCUMENTS    DOCUMENT   PUBLICATION DATE   Pages, Columns, Lines Where Relevant Passages or Figures Appear	